(A1)

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

G00002

(43) International Publication Date
29 August 2002 (29.08.2002)

PCT

(10) International Publication Number
WO 02/066714 A3

(51) International Patent Classification[7]: C30B 15/00, 29/06

(21) International Application Number: PCT/US02/01127

(22) International Filing Date: 2 January 2002 (02.01.2002)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
60/259,362 2 January 2001 (02.01.2001) US

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(81) Designated States *(national)*: CN, JP, KR, SG.

(84) Designated States *(regional)*: European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR).

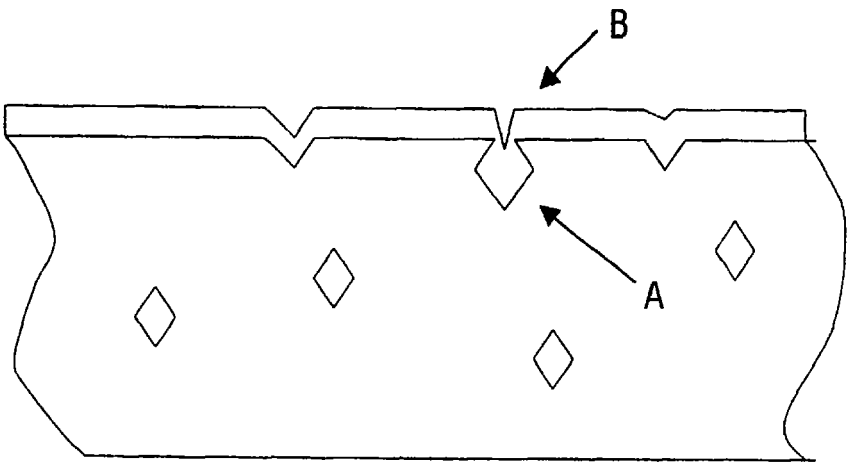
Published:
-- *with international search report*

(88) Date of publication of the international search report:
20 March 2003

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

162162

(54) Title: PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING IMPROVED GATE OXIDE INTEGRITY



(57) Abstract: A single crystal silicon wafer comprising a front surface, a back surface, a lateral surface joining the front and back surfaces, a central axis perpendicular to the front and back surfaces, and a segment which is axially symmetric about the central axis extending substantially from the front surface to the back surface in which crystal lattice vacancies are the predominant intrinsic point defect, the segment having a radial width of at least about 25% of the radius and containing agglomerated vacancy defects and a residual concentration of crystal lattice vacancies wherein (i) the agglomerated vacancy defects have a radius of less than about 70 nm and (ii) the residual concentration of crystal lattice vacancy intrinsic point defects is less than the threshold concentration at which uncontrolled oxygen precipitation occurs upon subjecting the wafer to an oxygen precipitation heat treatment.

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